TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

155383

LOW VOLTAGE HIGH SPEED SWITCHING

Small Package

• Composed of 2 independent diodes.

• Low Forward Voltage : V_{F(3)}=0.54V (TYP.)

• Low Reverse Current : $I_R = 5\mu A$ (MAX.)

MAXIMUM RATINGS (Ta = 25°C)

SYMBOL	RATING	UNIT
v_{RM}	45	V
$v_{ m R}$	40	V
$I_{ extbf{FM}}$	300*	mA
IO	100*	mA
$I_{ ext{FSM}}$	1*	A
P	100*	mW
T_{j}	125	$^{\circ}\mathrm{C}$
$\mathrm{T_{stg}}$	-55~125	$^{\circ}\mathrm{C}$
$T_{ m opr}$	-40~100	°C
	$egin{array}{c} V_{RM} \\ V_{R} \\ I_{FM} \\ I_{O} \\ I_{FSM} \\ P \\ T_{j} \\ T_{stg} \\ \end{array}$	$\begin{array}{c cccc} V_{RM} & 45 \\ V_{R} & 40 \\ I_{FM} & 300 ^* \\ I_{O} & 100 ^* \\ I_{FSM} & 1 ^* \\ P & 100 ^* \\ T_{j} & 125 \\ T_{stg} & -55 {\sim} 125 \\ \end{array}$

1. ANODE 1
2. ANODE 2
3. CATHODE 2
USQ 4. CATHODE 1
JEDEC —
EIAJ —
TOSHIBA 1-2U1A

Weight: 0.006g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Forward Voltage	V _{F (1)}	$I_{\mathbf{F}} = 1 \text{mA}$	_	0.28	_	V		
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$		0.36	_	V		
	$V_{F(3)}$	$I_{ m F} = 100 { m mA}$		0.54	0.60	V		
Reverse Current	$I_{ m R}$	$V_R=40V$		l	5	μ A		
Total Capacitance	C_{T}	$V_R = 0$, $f = 1MHz$	_	18	25	рF		

PIN ASSIGNMENT (TOP VIEW)



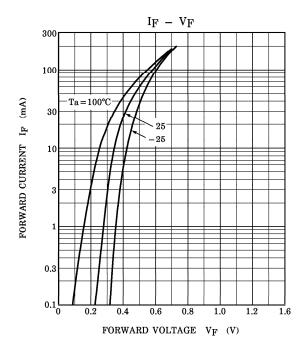
MARKING

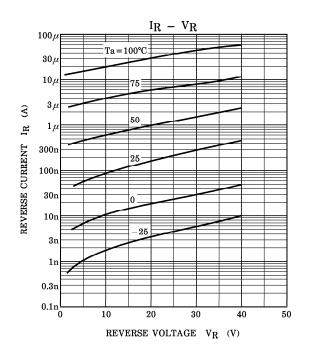


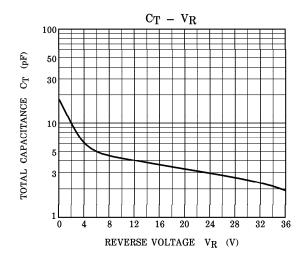
961001EAA2

^{* :} Unit Rating. Total Rating=Unit Rating×1.5

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.







The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

The information contained herein is subject to change without notice.